SG2M500120BH

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2 S

Table of contents

Features **1**

Benefits .....

1 Maximum ratings

Table 2 **Maximum rating** (Tc = 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{DS,max}$	Drain source voltage	1200	V	V_{GS} = 0V, I_D = 100μA	
$V_{GS,max}$	Gate source voltage	-8 /+19	V	Absolute maximum values	Note1
V_{GSop}	Gate source voltage	-4 /+15	V	Recommended operational values	
I_D	Continuous drain current	8 6	A	V_{GS} = 15V, T_C = 25˚C V	

SG2M500120BH

Datasheet

Q_{gs}	Gate source charge	-	2.1	-	nC	V_{DS} = 800V, V_{GS} = -4/+15V I_D = 2.5A	
Q_{gd}	Gate drain charge	-	3.6	-			
Q_g	Gate charge	-	9.6	-			

2.3 Switching characteristics

Table 6 Dynamic characteristics(Tc = 25°C unless otherwise specified,the data comes from TO-263-7L)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
E_{on}	Turn on switching energy	-	52	-	μJ	V_{DS} = 800V, V_{GS} = -4/+15V I_D = 2.5A, Rg = 2.5Ω L = 120μH	
E_{off}	Turn off switching energy	-	1.1	-			
$t_{d\ on}$	Turn on delay time	-	8	-	ns		
t_r	Rise time						

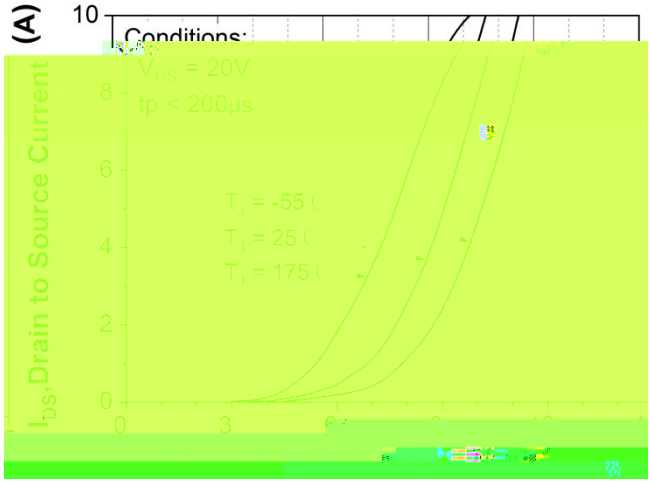


Figure 7. Transfer characteristic for various junction temperatures

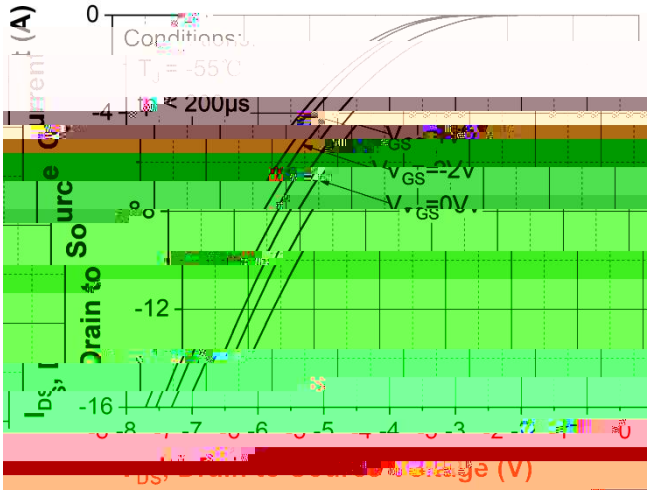


Figure 8. Body diode characteristic at T_J = -55 ºC

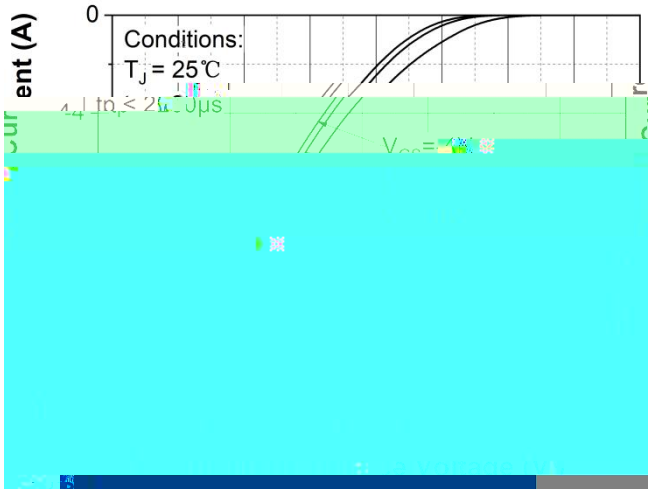


Figure 9. Body diode characteristic at T_J = 25 ºC

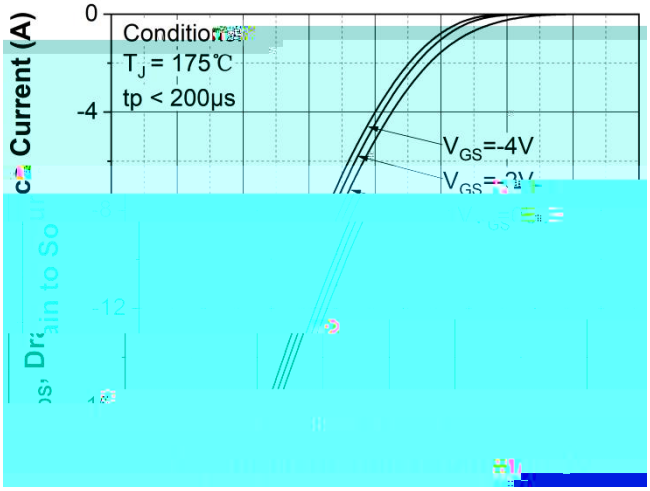


Figure 10. Body diode characteristic at T_J = 175ºC

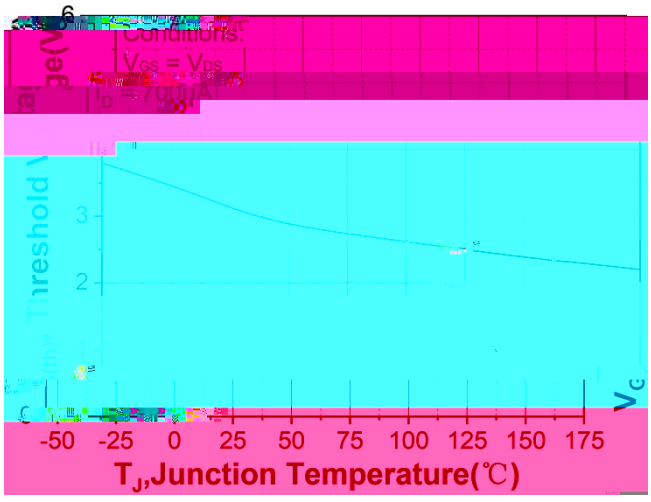


Figure 11. Threshold voltage vs. temperature

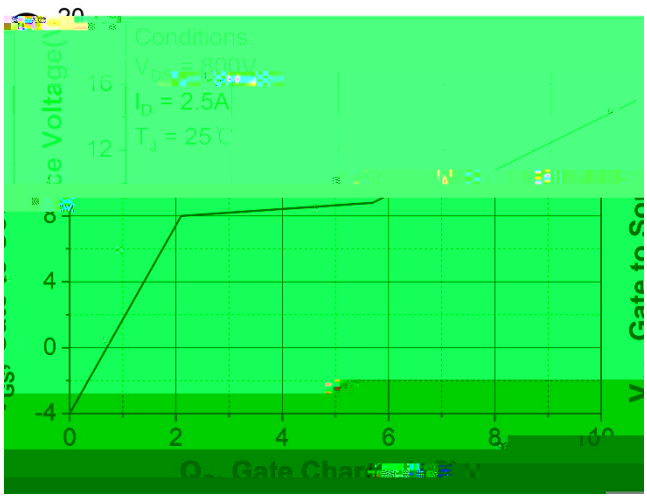


Figure 12. Gate charge characteristic

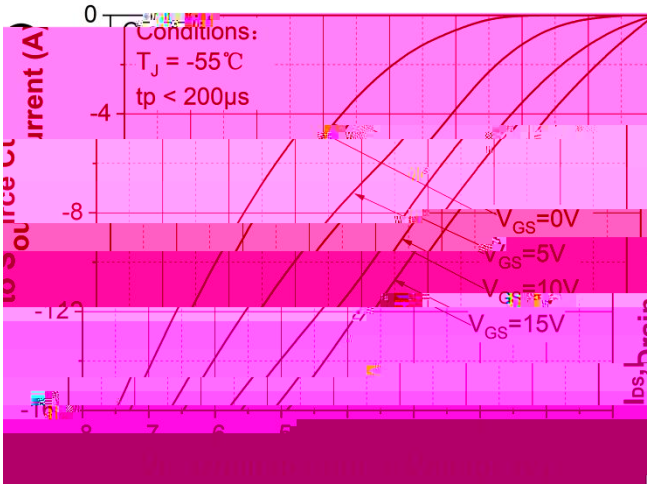


Figure 13. 3rd quadrant characteristic at T_J = -55 ºC

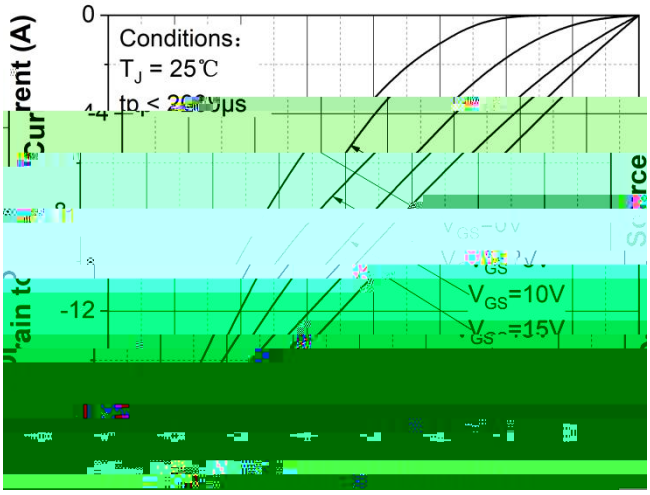


Figure 14. 3rd quadrant characteristic at T_J = 25 ºC

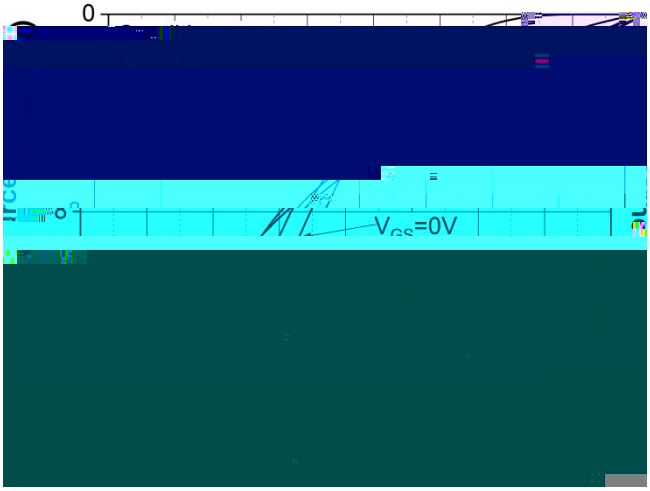


Figure 15. 3rd quadrant characteristic at T_J = 175 ºC

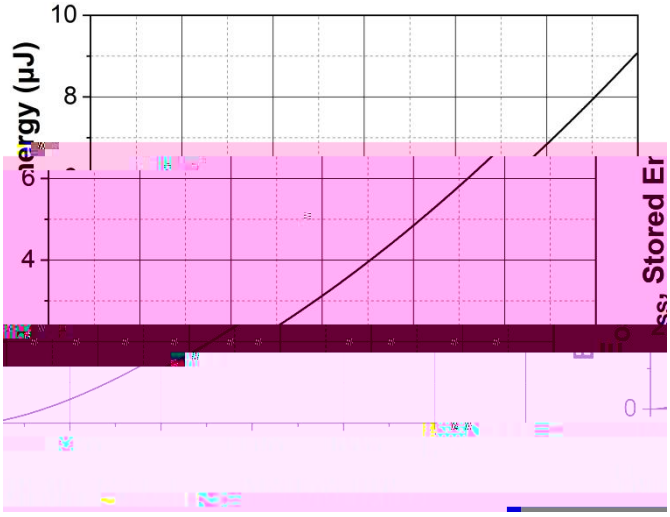


Figure 16. Output capacitor stored energy

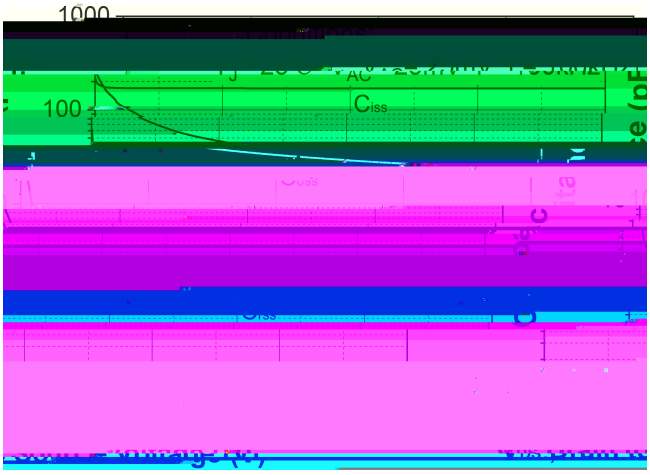


Figure 17. Capacitances vs. drain-source voltage (0 - 200V)

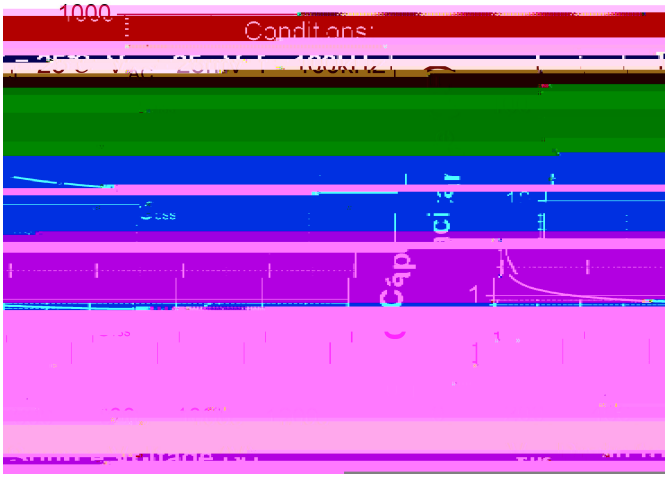


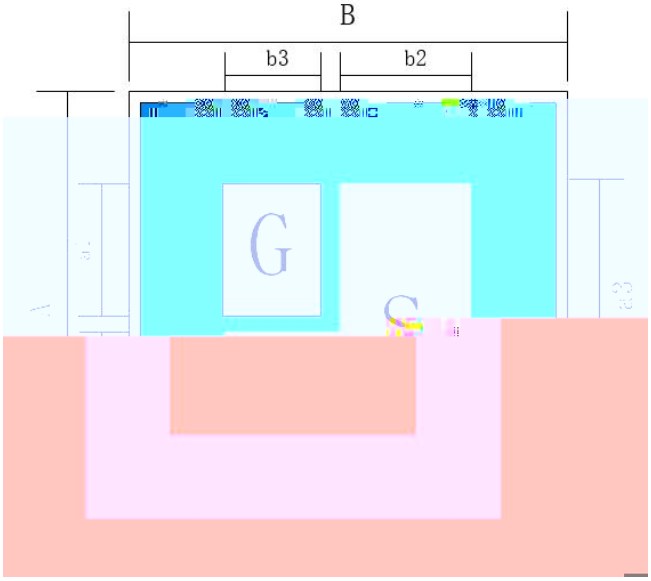
Figure 18. Capacitances vs. drain-source voltage (0 - 1200V)

4 Mechanical parameters

4.1 Dimensions and metallization

Parameter	Typical value	Unit	Metallization
Die size W x L	1.39 * 1.39	mm	
Gate pad size W x L	0.40 * 0.30	mm	
Die thickness	175	μm	
Top side source gate metallization	4	μm	Al
Back side drain metallization	1	μm	Ag

4.2 Layout



Symbol	Dimension / mm
B	1.39
b1	0.81
b2	0.43
b3	0.30
A	1.39
a1	0.40
a2	0.33
a3	0.81

5 Test conditions

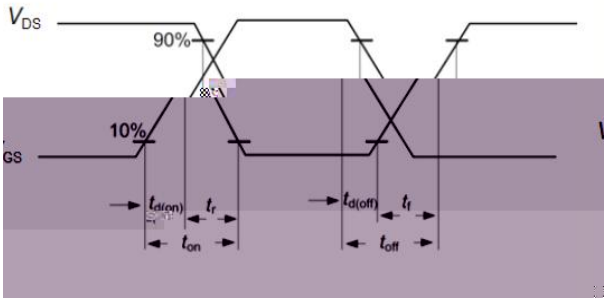


Figure A. Definition of switching times

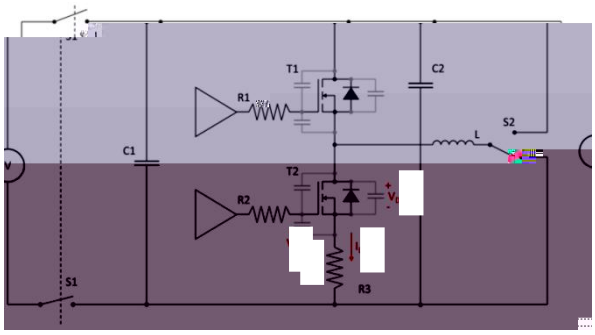


Figure B. Dynamic test circuit

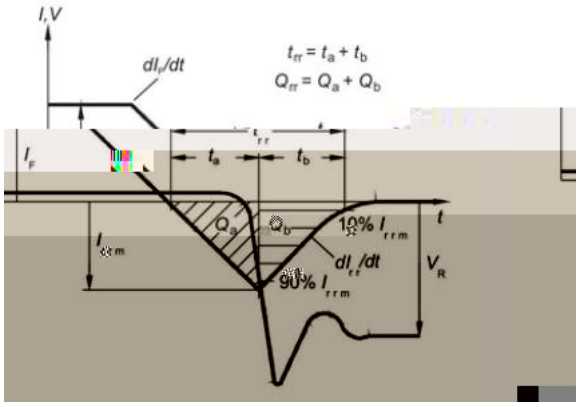


Figure C. Definition of body diode switching characteristics

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2025-09-19	——	——
V01_01	2025-12-26	Final	——

Attention

1. **Rohs compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/ EC (RoHS2), as implemented January 2, 2013.

2. **REACH compliance**

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Sichain representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

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